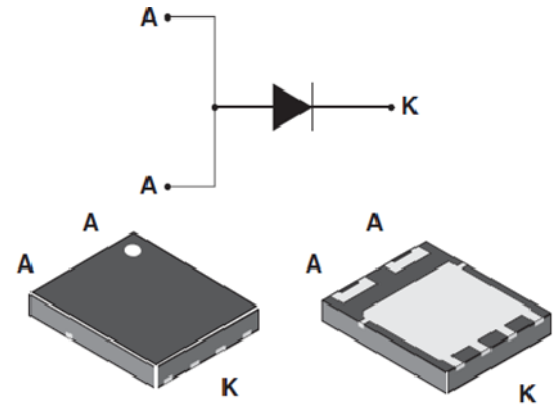


## Product Specification

**Ultra Low Vf=0.38V at IF=10A / Vf=0.25V at IF=1A/(25° C)**

GOODARK Type (POWER QFN Diode)  
SMBRP1045

Construction : Schottky Barrier Rectifier  
Application : For General Purpose  
(Manufacturer) :  
Suzhou Goodark Electronics Co.,Ltd  
Prepared on Aug. 18<sup>th</sup>, 2012  
Prepared: R & D Department  
Approva: QRA Department



### SCHOTTKY BARRIER RECTIFIER

10 AMPERES

45 VOLTS

**0.25V (1A Type)/ Ultra- Low Vf Schottky**

**0.38V (10A Type)/ Ultra-Low Vf Schottky**

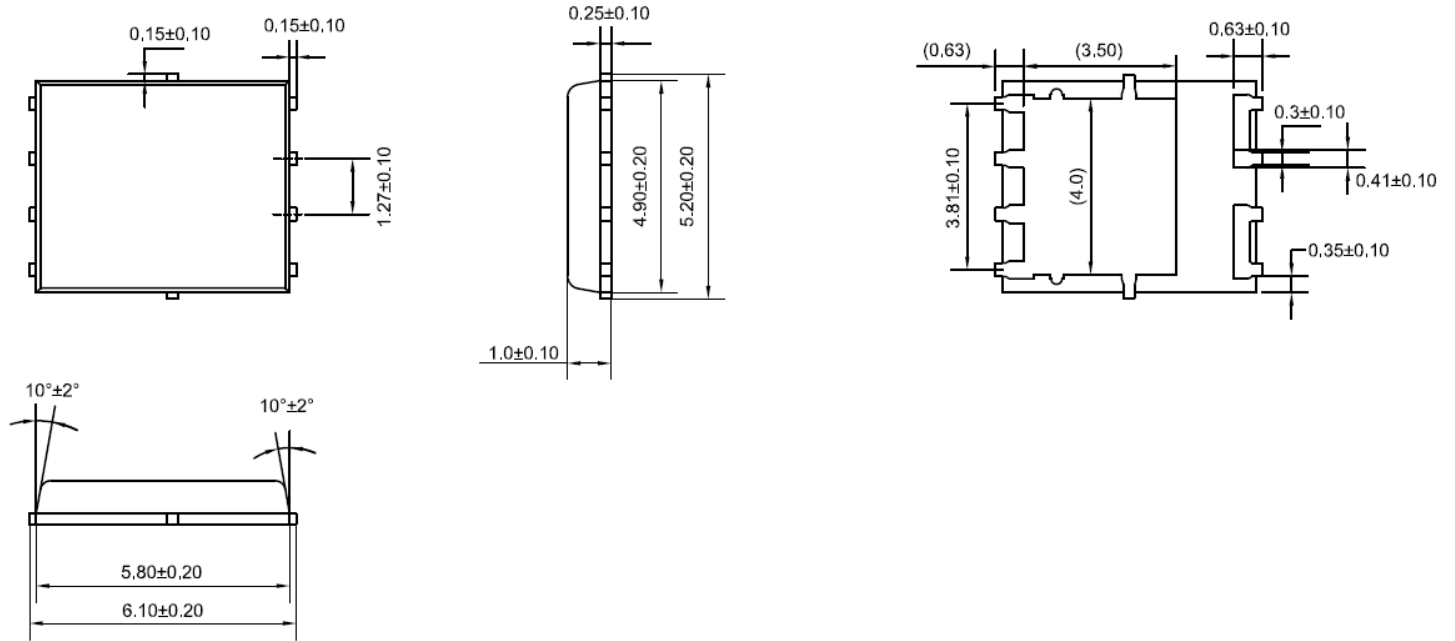
**Thin Package: 1.0mm**

**Halogen Free Package**

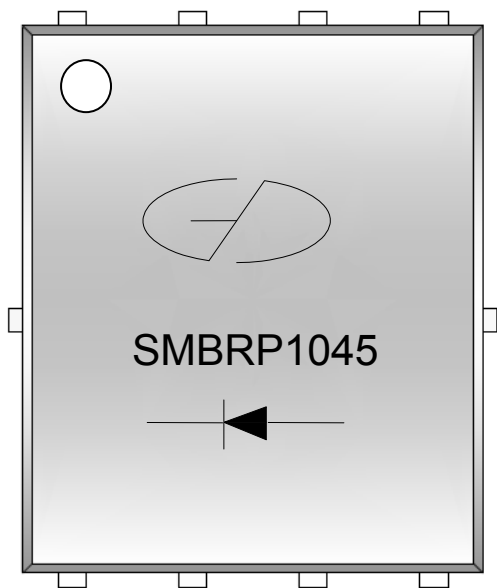
### CONTENTS

1. Package Outline
2. Marking
3. Features& Mechanical Characteristics
4. Maximum Ratings and Electrical Characteristics
5. Rating and characteristic Curves
6. Packing Specification PACKAGING SPECIFICATION
7. Description of Box Label

1. Package Outline (POWER QFN5X6)



2.MARKING

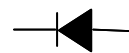


1. Part Name : SMBRP1045

2. Logo Mark:



3. Polarity:





### 3.Features& Mechanical Characteristics

#### Features

- Plastic package has underwriters Laboratory Flammability Classification 94V-0
- For surface mounted application
- Metal of silicon rectifier, majority carrier conduction
- Low forward voltage, high efficiency
- Guarding for over voltage protection
- For use in low voltage, high frequency inverters,
- Free wheeling, and polarity protection applications

#### Mechanical Characteristics

- Case: Epoxy, Molded
- Weight: 0.1grams (approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Shipped tape reel packing 3000/reel

### 4.Maximum Ratings and Electrical Characteristics

MAXIMUM RATINGS and ELECTRICAL CHARACTERISTICS(TC=25°C unless otherwise moted)					
PARAMETER	TEST CONDITIONS		SYMBOL	SMBRP1045	UNIT
Maximum repetitive peak reverse voltage			VRRM	45	V
Working peak reverse voltage			VRWM	45	V
Maximum DC blocking voltage			VDC	45	V
Maximum average forward rectified current at Tc=105°C total device per diode			IF(AV)	10	A
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load per diode			IFSM	250	A
Peak repetitive reverse current per leg at tp=2.0us , 1KHz			IRRM	1.0	A
Voltage rate of change (rated VR)			DV/dt	10000	V/us
Operating junction temperature range			TJ	—55 to+150	°C
Storage temperature range			TSTG	—55 to+150	°C
Maximum instantaneous forward voltage per leg	IF=1A IF=10A IF=10A IF=15A IF=15A	TC=25°C TC=25°C TC=125°C TC=25°C TC=125°C	VF	<b>0.25(Type)</b> 0.42/( <b>0.38Type</b> ) 0.33 0.46 0.39	V
Maximum reverse current per leg at working peak Reverse voltage	TJ=25°C TJ=100°C		IR	500 50	uA mA

#### Thermal Characteristics Ta=25°C unless otherwise noted

Symbol	Parameter	Max	Unit
RθJC	Thermal Resistance, Junction to Case per Leg	2.0	°C /W
RθJA	Thermal Resistance, Junction to Ambient per Leg	50	°C /W

#### Note:

1. Pulse test:300us pulse width, duty cycle=2%

### 5. Rating and Characteristic Curves

( $T_c=25^\circ\text{C}$  Unless otherwise noted)

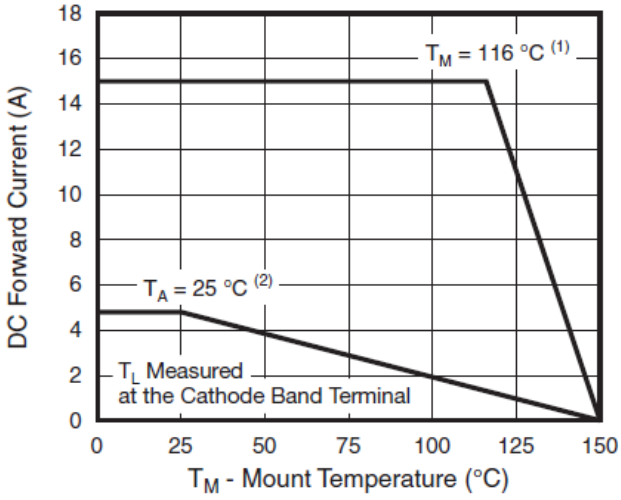


Fig. 1 - Forward Current Derating Curve

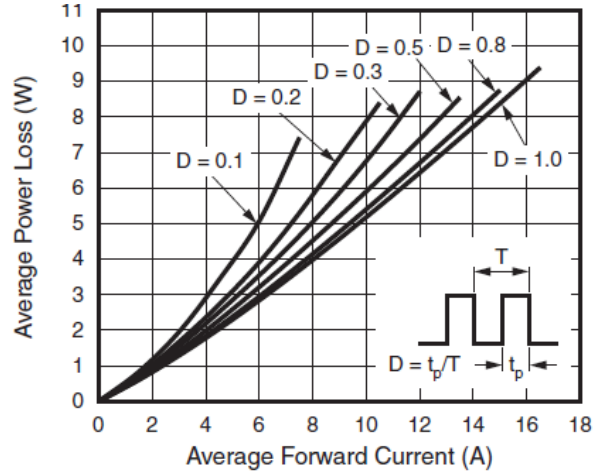


Fig. 2 - Forward Power Loss Characteristics Per Diode

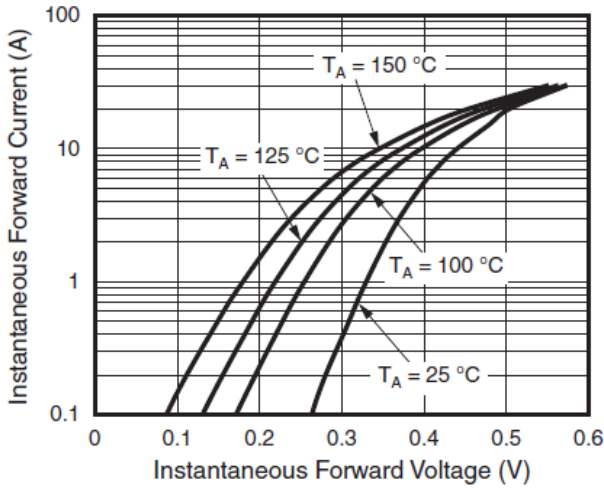


Fig. 3 - Typical Instantaneous Forward Characteristics Per Diode

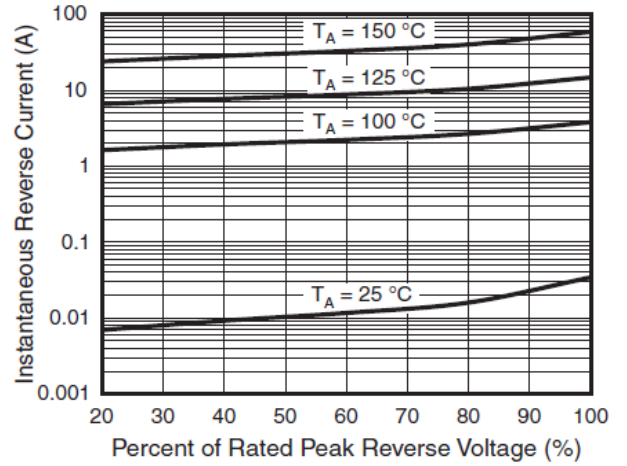


Fig. 4 - Typical Reverse Leakage Characteristics Per Diode

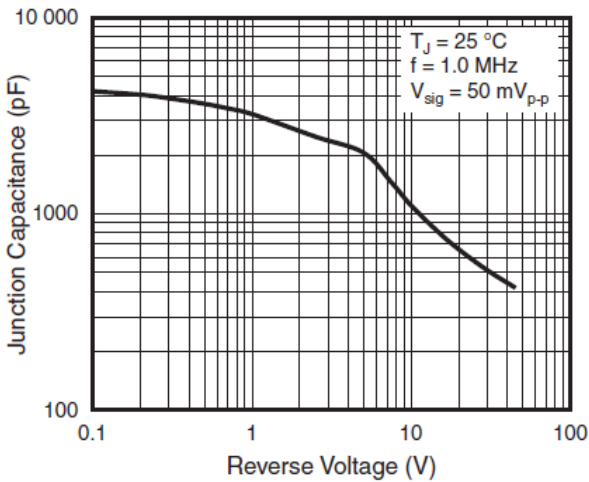


Fig. 5 - Typical Junction Capacitance

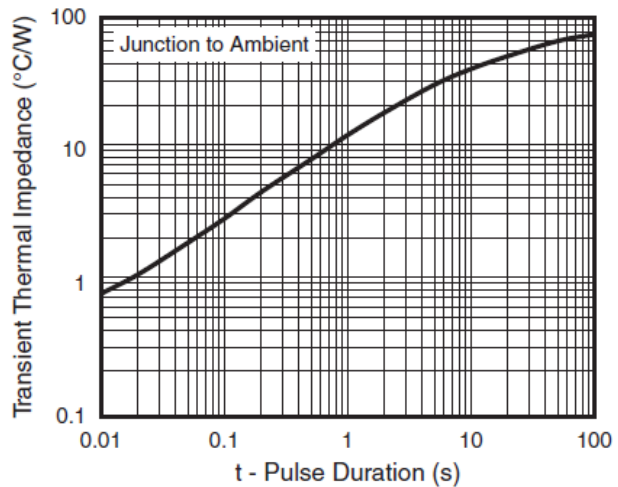


Fig. 6 - Typical Transient Thermal Impedance Per Diode



7. DESCRIPTION of BOX LABEL

	<p>TYPE:          Q'TY:          P/O NO:          LOT NO:</p>
<p>1) Inner Box Label</p>	<p>2) Inner Box Label</p>
	<p>TYPE:          Q'TY:          P/O NO:</p>
<p>3) Outer Box Label</p>	<p>4) Outer Box Label</p>